

Dynamic control of polarized thermal emission from VO₂ nanofins

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Abstract. Here we demonstrate switchable polarized thermal emission from VO₂ nano-fin stacks fabricated by co-deposition, etching and oxidation. We find that reverse switching of the thermal emission is enabled by a reflecting underlayer, induced by either short oxidation time or additional deposition of a reflecting underlayer. Observed thermal emission is well explained by a biaxial Bruggeman effective medium model, which predicts the strong polarization change for aligned fin layers in the micron thickness range. The dominant polarization of the emission is modulated by the presence of a reflector, oxidation of the fins, fin fill-factor, and structural anisotropy. Normal incidence polarized emittance change of up to 0.6 is theoretically possible, and we were able demonstrate a change of 0.34 similar to that predicted by the model.

Keywords: vanadium dioxide, polarization, thermal emission, nanostructured.

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1 Introduction

Dynamic control of thermal emission is an area of considerable interest, with application in areas such as thermal regulation, active camouflage, and sensing. A common strategy for varying thermal emission is to use phase change materials (PCM), such as Ge₂Sb₂Te₅(GST) or vanadium dioxide (VO₂), which have an associated change in their thermal infrared properties.

GST has been used for optical modulation due to a difference in reflectivity of its amorphous and crystalline phases.¹ GST has also been utilised for control of thermal emission including application in thermal camouflage and as a wavelength-selective and thermally stable IR emitter.^{2,3} However, while GST benefits from the stability of the crystalline phase, a consequential drawback is that it must be annealed above 640°C to return it to the amorphous state, which makes it unsuitable for some applications.⁴

In contrast VO₂ has a readily reversible transition near room temperature, and will be our focus in this article. The rapid insulator-metal transition can be activated by thermal, optical and

27 electrical stimulation.^{5,6} Several applications have made use of this functionality,⁷⁻¹⁰ in particular
28 modulated emission for thermal regulation.¹¹

29 The usual mechanism of emission control in VO₂ devices is that the bulk switches from high to
30 low emissivity on heating due to the increase in charge carriers, thereby reducing radiated heat.¹²
31 VO₂ is often used as a phase-changing material in or near photonic structures, for example for
32 adaptively enabling radiative cooling, depending on the ambient temperature.¹³ Likewise, by using
33 ~150 nm of VO₂ on sapphire Kats et al. were able to display a near "perfect" black body emittance
34 at a single wavelength. This was achieved through the insulator to metal transition (IMT) of VO₂.
35 Interestingly, the intermediary state of the VO₂ consists of nanoscale islands of conducting and
36 insulating phases, acting as a natural, disordered meta-material,¹⁴ which is readily modelled with
37 a Bruggeman effective medium model.^{15,16}

38 Recent attention has focused on inverted emission switching (increasing with heating), allow-
39 ing abruptly increased radiative cooling and enhanced temperature regulation. Inverted switching
40 has been achieved by structuring including multi-layers,^{17,18} lithography,^{19,20} and self-assembly.²¹
41 In our recent work, vanadium oxide nano-fins were produced by a lithography-free method con-
42 sisting of co-deposition with aluminum followed by chemical removal of the aluminum and then
43 gaseous oxidation. Varying fin height achieved a variety of switching profiles, including reverse
44 switching.

45 A similar method was used in a different paper to produce Mo fins which were shown to
46 be heat-stable polarizers.²² Therefore it is expected that VO₂ fins (such as those seen in Fig.1),
47 would enable switchable polarized thermal emission near the normal direction, with applications
48 such as infrared instrumentation. So far, comparatively little progress has been made towards
49 this functionality. One relevant work²³ demonstrated a different approach using elliptical metal

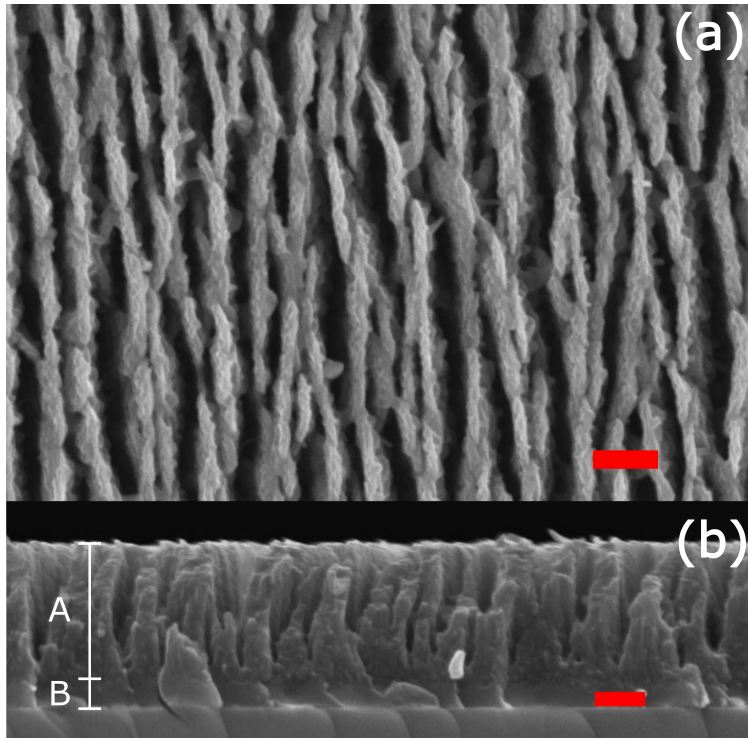


Fig 1 SEM image of a typical nanostructured VO_2 thin film on glass. (a) showing top view and (b) showing the cross-section view. (Scale bar 200nm). The polarization convention used in this article refers to the in-plane fin axes, i.e. perpendicular is left-right in both panels, parallel is top-bottom in (a). In (b) 'A' indicates the fins while 'B' indicates the native reflector.

50 patches on GST, with simulations predicting up to 0.7 absolute emittance difference and high
51 ratio. However, that design required lithography, and measured performance was only about 0.1
52 absolute difference and ratio ~ 2 . Furthermore, this polarizing surface is unable to function near
53 normal angles.

54 The approach that we present in this article does not require lithography, achieves high abso-
55 lute polarization over a comparatively broad spectral range, operates at near normal angles and
56 demonstrates reversible switching at modest temperatures.

57 We first demonstrate the ability to choose the direction of the switch by controlling the oxida-
58 tion state, then predict how the switch can be reversed and optimized by simple geometric changes,
59 and finally demonstrate strongly polarized emission.

60 **2 Experimental**

61 We produced VO₂ nano fins using a three-step process:²¹ self-assembly of V-Al fins, dissolution
62 of Al using NaOH to form vanadium fins, followed by controlled oxidation during annealing. First
63 V-Al fins were produced by co-sputtering of V and Al. The targets were spaced 150 mm apart
64 from one another with a 37 °angle to the stage normal at the center of the target, with an angular
65 spread (30°-46°) due to target size. The alloy fins were placed into 1 M NaOH for 13 minutes to
66 selectively etch the Al from the alloy, leaving V fins, similar to our previous work.²² The final step
67 in production was the oxidation of the fins by annealing in sub-atmospheric (0.2 Torr) air. A carbon
68 heating block maintained the films at approximately 500° for several hours to produce the desired
69 VO₂ phase. In some samples, 200 nm of pure vanadium was deposited on the substrate before the
70 nanofin structure was deposited. The switching of thermal emission on heating and cooling from
71 30 to 80 °C was measured via three techniques: (1) spectrally-integrated unpolarized emission,
72 (2) infrared reflectance and (3) spectrally-resolved polarized emission measurements. Method 1
73 - The integrated measurements were estimated from the apparent radiant temperature T_{IR} using
74 equation 1. It is important to account for the sample temperature and reflected temperatures to
75 accurately determine the emittance of the surface being tested. Using an infrared sensor that returns
76 a temperature measured in Kelvin we can use Equation 1 to determine the emittance of the sample
77 E and temperature.²¹

$$\epsilon(T) = \frac{T_{IR}^4 - T_{Reflected}^4}{T_{Sample}^4 - T_{Reflected}^4} \quad (1)$$

78 This method provides a fast technique to assess a sample's temperature-dependent emittance per-
79 formance, for example in Fig 3, prior to detailed temperature-dependent spectral measurements of

80 a sample.

$$\epsilon(T) = \frac{\int A(\lambda) * B(\lambda, T)d\lambda}{\int B(\lambda, T)d\lambda} \quad (2)$$

81 Likewise once the spectral properties of a surface are known we can use Equation 2 to calculate
82 the temperature dependent emittance. $E(T)$ is the integrated emittance, $A(\lambda)$ is the absorption
83 properties of the surface and $B(\lambda, T)$ is the black body Planck spectrum for each wavelength(λ) and
84 temperature(T). In the case of temperature dependent optical properties $A(\lambda, T)$ can be substituted
85 in for $A(\lambda)$. Equation 2 can be used to compare results measured via Method 2 and Method 1.

86 Method 2 - FTIR (Fourier Transform Infrared) reflection spectroscopy was performed with
87 a Perkin-Elmer Spectrum 100 FT-IR Spectrometer with a Harrick SeaGull variable-angle reflec-
88 tion stage (modified with a sample heating stage) and infrared wire-grid polarizer in a 2.5-25 μm
89 wavelength range, with incidence angles varying from 10 to 45°. Samples were measured at 25°C
90 and 90°C (cold and hot states). These reflection measurements were performed on both solid
91 and structured films, and were used to establish model parameters and to validate direct emission
92 measurements.

93 The ellipsometric software WVASE, by JA Woollam Co, was used to fit the complex refractive
94 index of each of the solid thin film samples (VO_2 in both the cold “semiconducting” and hot
95 “metallic” states, thin film sputtered vanadium and glass substrates), with generalized oscillator
96 models produced for each material.

97 The nano-fin structure was modelled by a biaxial Bruggeman effective-medium layer with
98 geometric depolarization factors for in-plane and stack directions.²⁴ This is a well-established
99 model that we have successfully applied to similar structures in earlier work. Bulk VO_2 properties
100 for hot and cold states were based on fits to solid thin films. To ensure consistency of geometric

101 parameters, fitting of the fill factor and depolarization factors in the biaxial Bruggeman model was
102 simultaneously conducted in both the low and high temperature states with parameters linked.

103 The intermediate temperature response of the bulk VO₂ was incorporated using a Bruggeman²⁵
104 effective medium model, as suggested in.^{15,16} A sigmoidal model was used to fit $f(T)$ the fraction
105 of solid material which has undergone the transition into the metallic state for each temperature.
106 This was supported by additional temperature dependent ellipsometry from 0.3 - 3 microns (Wool-
107 lam V-VASE with custom temperature stage).

$$f(T) = \frac{e^{(T-T_c)*P_1}}{e^{(T-T_c)*P_1} + 1} \quad (3)$$

108 For brevity, a simplified symmetric form of the sigmoidal function is presented in Equation 3. This
109 equation can be fitted to measured data to represent the relationship between Bruggeman effective
110 medium fill factor and sample temperature. Further parameters can be added to the function to
111 enable modelling of samples with an asymmetric transition. Here the parameters represent the
112 transition temperature, T_c , and the width of the transition is set by P_1 . Typical values to model the
113 VO₂ transition are in the order of $T_c = 340$ and $P_1 = 0.4$.

114 Combining the biaxial effective medium (structural model) with the temperature-dependent
115 VO₂ optical constants simulates the full optical response of the nanofin stack as it is heated through
116 the IMT. Equilibrium emission in the normal direction is readily estimated from the normal inci-
117 dence reflectance at each polarization and temperature weighted by the Planck blackbody spec-
118 trum. Predicted emission can be compared with the polarised emission measurements collected
119 with the custom FTIR setup discussed next.

120 Method 3 - spectrally-resolved polarized emission measurements were carried out with a cus-

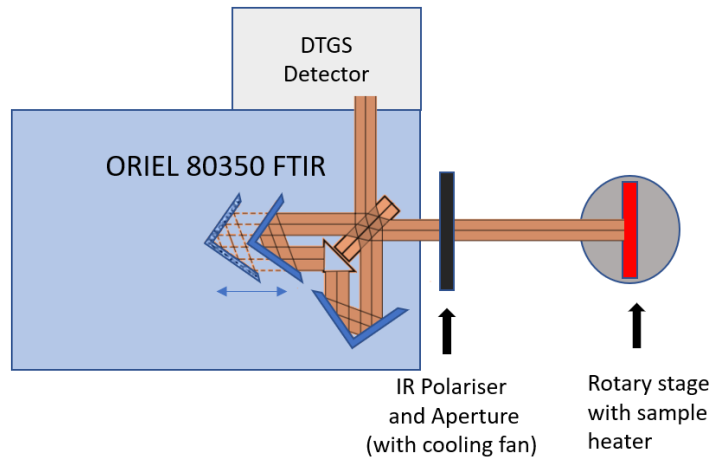


Fig 2 Schematic of FTIR setup for polarised emission measurements. The detector is an ambient-temperature dTGS.

121 tomized Oriel 80350 FTIR (Fourier transform infrared) spectrometer, in which the infrared source
 122 was replaced with a sample heater attached to a variable angle stage and rotating infrared wire-
 123 grid polarizer. Fig 2 displays a schematic of the customised FTIR setup utilised to take the direct
 124 emission measurements. We note that it is important to consider instrument configuration and
 125 calibration when measuring emittance.²⁶

126 An ambient-temperature dTGS(triglycine sulfate) detector is utilised with a heated sample
 127 stage. Rather than controlling the stage temperature, the sample temperature is measured with
 128 a low thermal mass type-K thermocouple clamped on the front surface of the sample to minimise
 129 any variance in the temperature gradient throughout the sample/stage. The FTIR emission was
 130 calibrated using the measured temperature dependent emission from glass substrates with spectral
 131 properties established by reflection FTIR.

132 The background signal was minimised by the use of a large sample size of 75 mm x 50 mm
 133 and an aperture placed before the polarizer. Aperture and polarizer were kept near ambient by fan-
 134 forced convection. The use of a system with a room temperature dTGS detector, rather than a liquid
 135 nitrogen cooled mercury cadmium telluride (MCT) detector, dramatically simplifies calibration

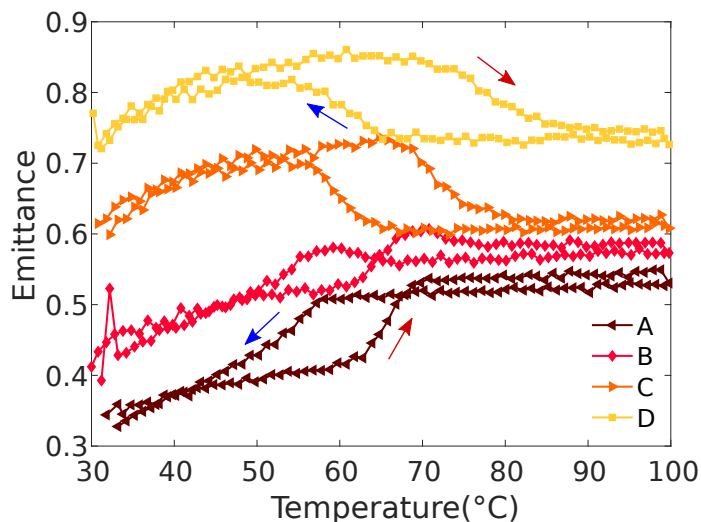


Fig 3 Integrated thermal emittance switching of VO₂ nano fins for increasing anneal times (A 4 hrs to D 11hrs) at 500°C in 0.2 Torr air. Red arrows indicate heating and blue are cooling.

136 because ambient temperature sources (such as optical components and reflections) produce zero
 137 signal. Since the heated sample acts as the source, emission measurements were performed at a
 138 minimum of 30 °C (~ 10 °C above ambient) to ensure sufficient signal. Temperature step times
 139 were chosen to ensure equilibrium was achieved. This system has been previously validated against
 140 reflection measurements across a wide range of temperatures with various temperature independent
 141 samples.

142 3 Results and Discussion

143 The switching of unpolarized spectrally-integrated emittance is an important first test in under-
 144 standing the potential of these structures. We have discovered that the annealing time in air has a
 145 major effect on the emission switching profiles, with the final oxidized state having “regular” high-
 146 to-low emissivity switching. Fig. 3 shows the effect of temperature on the emittance of various
 147 samples annealed for differing times, with reverse switching only seen at shorter times. Here the
 148 unpolarised spectrally-integrated thermal emittance (Method 1) is used to measure each sample.

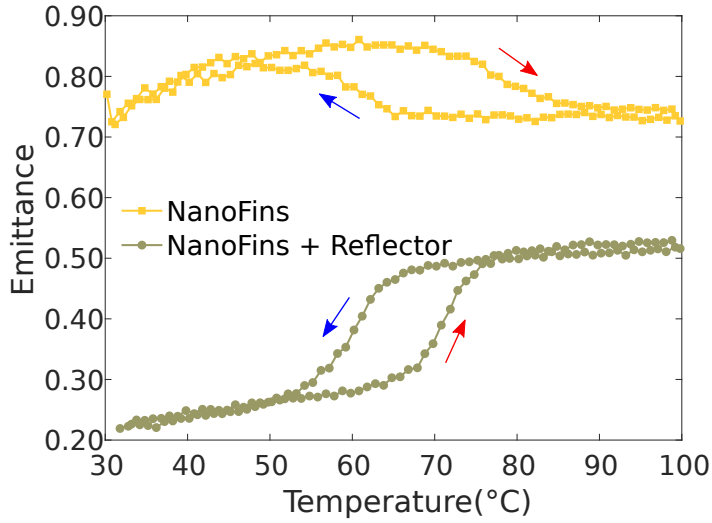


Fig 4 Integrated emittance switching of fully oxidized nano fins alone (yellow) and with an additional reflector (green). Both samples are annealed for 11 hrs at 500°C in 0.2 Torr air. Red arrows indicate heating and blue are cooling

149 Since the fin production method typically leaves a solid underlayer, we propose that a nearly
 150 metallic V underlayer contributes to reverse switching at short oxidation times. To test this hypoth-
 151 esis, we added an additional 200nm thick V layer prior to deposition of the fins. As expected, the
 152 additional reflector reversed the switching direction for the longer anneal times (fully oxidized fins
 153 layer), as seen in Fig. 4. The magnitude of the emissivity changes are -0.13 and +0.30 for the fins
 154 alone and fins+reflector respectively, showing the potential from improved switching magnitude
 155 in addition to reversing the direction. In contrast, Fig.5 shows the how little the emittance of less-
 156 annealed samples is affected by an additional reflector. In both cases the emission switch is +0.25
 157 which is somewhat less than the fully-oxidized fins with additional reflector. The negligible effect
 158 of the reflector on partially-oxidized fins is also consistent with the hypothesis that the underlayer
 159 is a major contributor to switching reversal, since those films retain a native metallic underlayer.

160 A fitted optical model is valuable for understanding and assessing the full potential of emission
 161 from these structures. Variable-angle polarized infrared reflection spectra, measured via Method 2,
 162 were fitted to a biaxial effective-medium model to estimate the nanofin structure and the underlayer

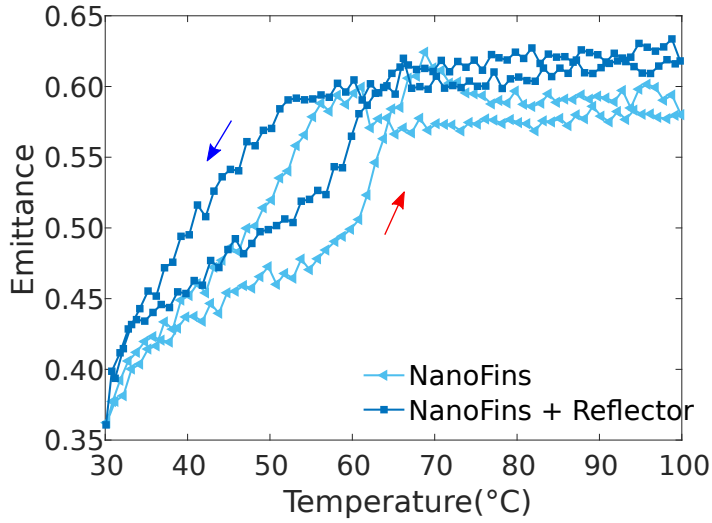


Fig 5 Integrated emittance of reverse switching fins (light blue), and with the addition of a 200nm vanadium base reflector (dark blue). Both were annealed for 4hrs. Red arrow indicate heating and blue is cooling.

Layer	Material	Short Anneal	Long Anneal
3	biaxial Bruggeman (VO ₂ /void)	0.80μm 53 % VO ₂ depol (L =0.29, L _⊥ =0.71, L _{stack} =0.00)	0.61μm 20% VO ₂ depol (L =0.18, L _⊥ =0.59, L _{stack} =0.23)
2	bulk VO ₂	-	0.17μm
1	Vanadium	0.10μm	-
Substrate	Glass	1 mm	1mm

Table 1 Optical fit parameters of representative nanofin stacks with short and long anneal times.

163 thickness. The material optical properties used were that of solid thin films. Table 1 summarizes
 164 the parameter values determined for the 4 hr and 11 hr annealing times. Here Layer 3 represents
 165 the fin structure, with a biaxial Bruggeman effective medium approximation. The table includes
 166 the thickness, volume fraction of VO₂ and the biaxial depolarization factors which represent the
 167 shape of the fin structures.

168 Spectrally-resolved polarized emission measurements - Method 3, demonstrate the broad spec-
 169 tral range of these structures. Fig. 6 shows the normal emission radiance in temperature-wavelength
 170 space for parallel and perpendicular polarizations and their difference, comparing experimental
 171 emission measurements and with simulation based on the biaxial-Bruggeman model which was

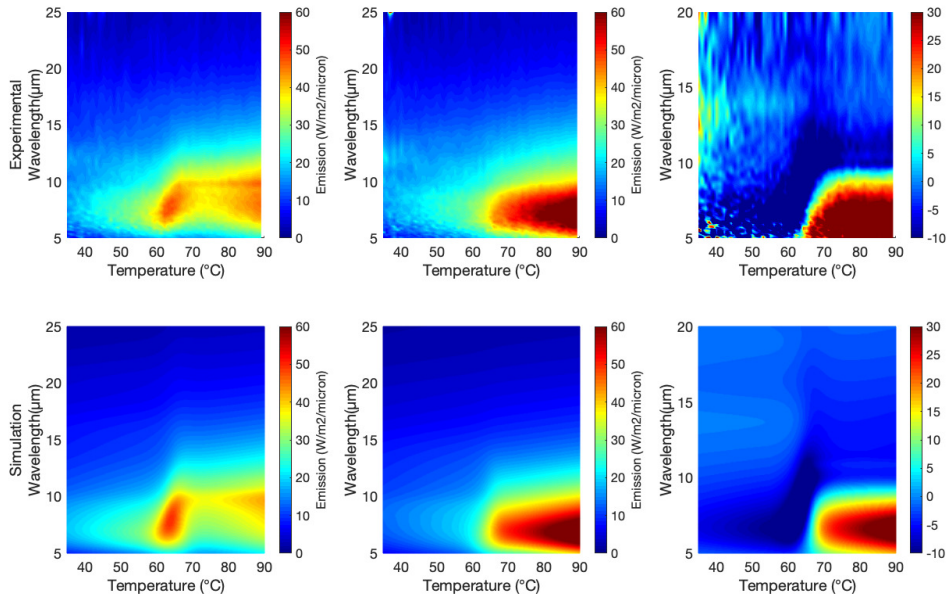


Fig 6 Polarized emission spectra as a function of temperature for a partially-oxidized nanofin stack, comparing measured experimental values (top row) and simulation model (bottom row). Left-most figures display the emission for the parallel polarization, middle figures indicate the perpendicular polarized emittance. Right figures display the polarization difference.

172 fitted to the infrared reflectance spectra. A large change in the emissions is observed in the 5-
 173 12 μm wavelength range, which is especially relevant to near-ambient thermal emission. In the
 174 parallel polarization a switch at $\sim 65^\circ\text{C}$ is also observed in the same wavelength range, although
 175 the change is smaller and at some wavelengths is reversed. Fig.6 displays the difference between
 176 the polarizations: the largest difference was observed for the hot state in the 5-10 μm wavelength
 177 range. The good match of the emissivity contours confirms the validity of the model used in the
 178 simulations.

179 The validated optical model for the nanofins can be used to assess the effect of various pa-
 180 rameters and the maximum possible polarized emission switch. The calculated absorptance can
 181 be used to predict the temperature-induced (hot and cold state) change in the difference between
 182 normal-emittance for polarizations along and across the fins $(e_{H\parallel} - e_{H\perp}) - (e_{C\parallel} - e_{C\perp})$, which we will

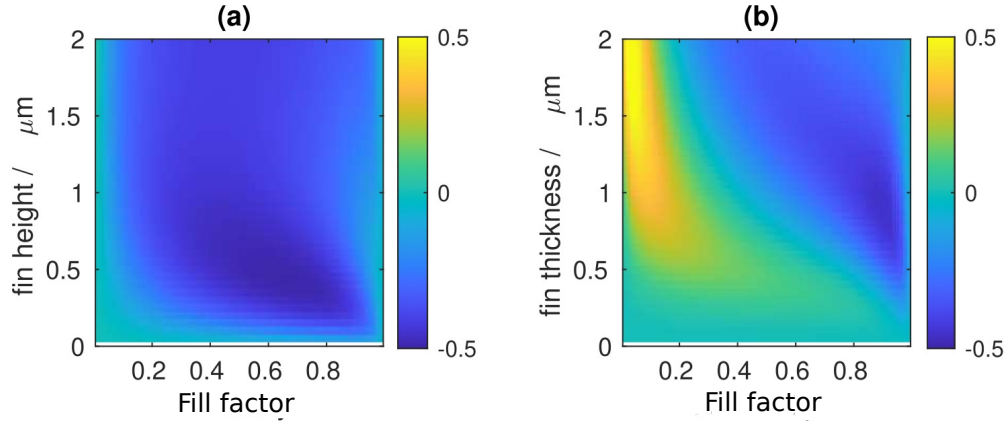


Fig 7 Maps of the "polarized emittance change" for depolarization ($L_{\parallel}=0$, $L_{\perp}=1$, $L_{stack}=0$) as a function of fin fill-factor and layer thickness, (a) without and (b) with reflector.

183 refer to as "polarized emittance change". This metric has a maximum magnitude of ± 2 , and has
 184 been selected because it is unambiguously defined under spectral integration.

185 It is known that a biaxial Bruggeman model with extreme values of depolarization factors
 186 ($L_{\parallel}=0$, $L_{\perp}=0$) will usually have optimum in-plane polarization, so we can focus on the effect of
 187 the fill-factor (the amount of VO_2) and fin height, both with and without an underlying reflector.
 188 Fig. 7 demonstrates that, assuming sufficient height (e.g. ~ 1 micron), the fill-factor of the fin layer
 189 has the most important effect on the polarization change. In the absence of an underlying reflector,
 190 the model predicts that heating will decrease the parallel polarization (-0.50 polarization change)
 191 at moderate fill-factors. With an underlying reflector, at low fill-factors the parallel polarization
 192 increases (+0.64 polarization change), whereas at high fill-factors the perpendicular polarization
 193 increases (-0.48 polarization change).

194 Further analysis reveals the details of the polarization response, summarized in Fig. 8. In
 195 the cold state (not shown), the fins are mostly unpolarized and transmitting, so the stack response
 196 is mostly unpolarized and determined by the underlayer (emitting or reflecting), whereas in the
 197 hot state the fin response also becomes important. The hot fins interact most strongly with the

198 parallel polarization: at low fill-factor they strongly emit (and moderately transmit) this polar-
199 ization, whereas at moderate to high fill-factor they strongly reflect (and moderately emit) this
200 polarization. The perpendicular polarization is mostly transmitted through the fins except at high
201 fill-factor where the fins are moderately reflecting. If the underlayer is emitting, maximum polar-
202 ization occurs at moderate a fill-factor, since parallel polarization is reflected and perpendicular is
203 transmitted, leading to reduced parallel (and average) emittance. If the underlayer is reflecting, the
204 hot stack emittance depends strongly on fin fill-factor. At low fill-factor, the hot fins emit some
205 parallel polarization but do not couple to perpendicular, so the parallel (and average) emittance
206 increases. Conversely at high fill-factor, the hot fins couple more to both polarizations but reflect
207 mostly parallel, eventually resulting in a moderate increase of perpendicular emittance. The fitted
208 experimental values of depolarization are not as extreme, with values (0, 0.29, 0.71) and (0.23,
209 0.18, 0.59) for the shortest and longest oxidation times respectively. However, Fig. 9 shows that
210 if it were possible to optimize the fill-factor accordingly, the polarization change would be almost
211 as strong as maximum depolarization. The samples used for developing the model with relatively
212 shallow (0.6 to 0.8 μm) thickness and had relatively weak polarization change, e.g. sub-oxide with
213 polarization change of only -0.04, and an oxide sample improved and reversed from -0.09 to +0.19
214 with the addition of a reflecting vanadium underlayer.

215 A thicker sample (black dot) had much stronger performance (-0.34). Although this thicker
216 sample had a long oxidation, its visible backside reflectance, top-side color, spectral response
217 and integrated performance were all consistent with VO_2 structure with a remnant non-oxidized
218 reflecting vanadium underlayer. This highlights the importance of calibrating oxidation times to
219 account for deposition parameters.

220 The VO_2 nano-structured films tested here showed no degradation during temperature-induced

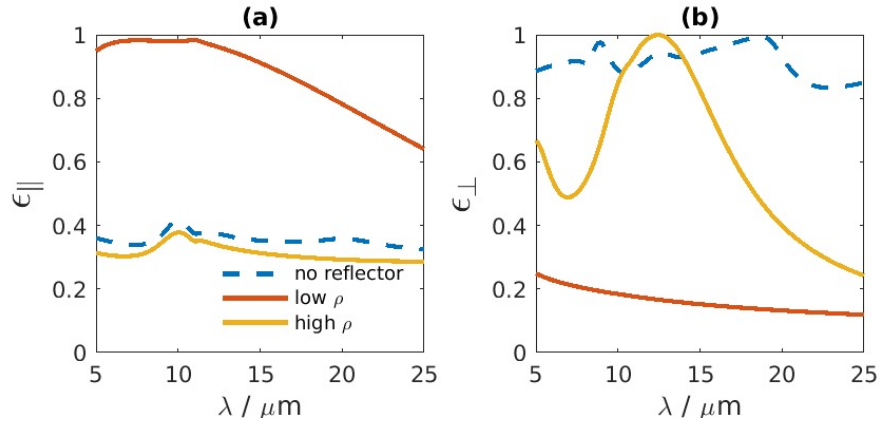


Fig 8 Predicted hot emittance spectra of optimal stacks, polarized (a) parallel and (b) perpendicular to the fins. Depolarization was ($L_{||}=0, L_{\perp}=1, L_{stack}=1$). One result lacks a reflector (fin fill-factor 0.66 and height 0.45 microns), and the other two have a 1 micron V reflector (one with fin fill-factor 0.02 height 2.85 microns, and the other with fill-factor 0.90 and height 0.90 microns)

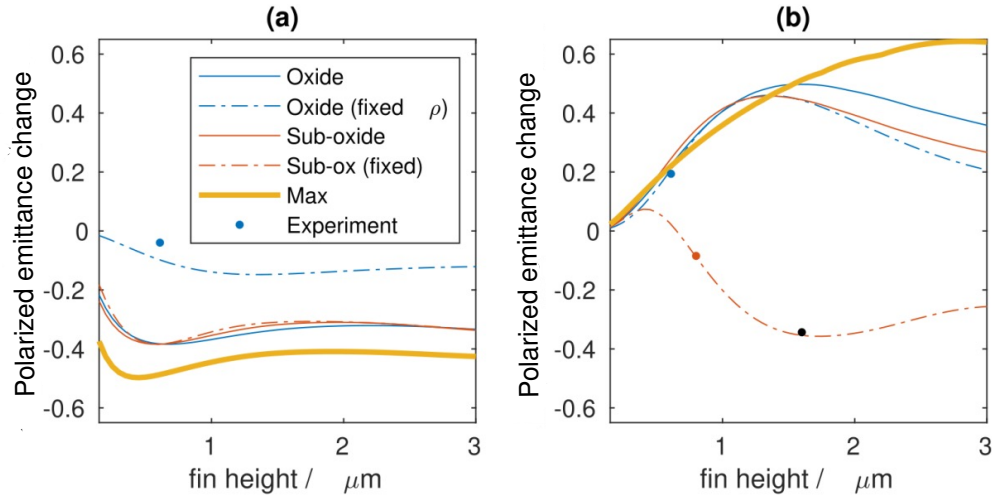


Fig 9 Predicted effect of fin layer height under various constraints, (a) without and (b) with reflector. "Max" has extreme anisotropy and optimal fill-factor for a given height. "Sub-oxide" corresponds to the shortest oxidation time, with optimal and experimental (fixed) fill-factor; "Oxide" corresponds to the longest oxidation time. Various experimental samples are shown as markers.

221 phase transition. Samples were cycled many times during differing testing runs and no change in
222 response was observed. The samples were also observed to be shelf-stable and samples were still
223 able to perform after many months of being stored in ambient conditions.

224 **4 Conclusion**

225 In summary the model clearly demonstrates the effect of the reflecting underlayer in reversing the
226 polarization change, that polarization performance is sensitive to fill-factor (with changes occur-
227 ring in either polarization), and that optimum performance can be achieved by fin layers around
228 1.5 micron thick. The annealing time is especially important because partial oxidation reverses
229 the switching direction (due to unoxidized underlayer), and full oxidation restores the direction.
230 Adding a metallic reflector to fully-oxidized fins also reverses the switch and produced a strong
231 unpolarized emittance change (+0.30), at least doubling cooling power above the transition tem-
232 perature. A biaxial effective medium stack provides an accurate model of the observed behavior
233 and indicates a metallic underlayer when oxidation is incomplete. Direct emission measurements
234 confirm a strong positive emission increase in the 5-12 μ m band for the polarization aligned with
235 the fins for an incompletely oxidized layer. Optimization using the nanofin model predicts the
236 importance of underlayer reflection, fin fill-factor and thickness, with a strong polarization change
237 of 0.34 confirmed for sufficiently thick films.

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323 List of Figures

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